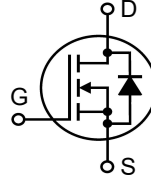


X4-Class Power MOSFET

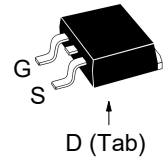
IXTA60N20X4

$V_{DSS} = 200V$
 $I_{D25} = 60A$
 $R_{DS(on)} \leq 21.0m\Omega$

N-Channel Enhancement Mode
Avalanche Rated



TO-263
(IXTA)



G = Gate D = Drain
S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|--------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 200 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 200 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | 60 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 106 | A |
| I_A | $T_C = 25^\circ C$ | 30 | A |
| E_{AS} | $T_C = 25^\circ C$ | 350 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 50 | V/ns |
| P_D | $T_C = 25^\circ C$ | 250 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| F_C | Mounting Force | 10..65 / 2.2..14.6 | N/lb |
| Weight | | 2.5 | g |

Features

- International Standard Package
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 200 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.5 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 5 μA 300 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 17.6 | | 21.0 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|-------------------------------------|--|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 34 | 56 | S |
| R_{Gi} | Gate Input Resistance | | 7.45 | Ω |
| C_{iss} | } $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 2450 | pF |
| C_{oss} | | | 406 | pF |
| C_{rss} | | | 0.95 | pF |
| Effective Output Capacitance | | | | |
| $C_{o(er)}$ | Energy related } $V_{GS} = 0\text{V}$ | | 240 | pF |
| $C_{o(tr)}$ | Time related } $V_{DS} = 0.8 \cdot V_{DSS}$ | | 880 | pF |
| $t_{d(on)}$ | } Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External) | | 13 | ns |
| t_r | | | 22 | ns |
| $t_{d(off)}$ | | | 52 | ns |
| t_f | | | 10 | ns |
| $Q_{g(on)}$ | } $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 33 | nC |
| Q_{gs} | | | 9 | nC |
| Q_{gd} | | | 11 | nC |
| R_{thJC} | | | | 0.60 $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|-------|
| | | Min. | Typ. | Max |
| I_S | $V_{GS} = 0\text{V}$ | | | 60 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 240 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.4 V |
| t_{rr} | } $I_F = 30\text{A}$, $-di/dt = 200\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ | | 107 | ns |
| Q_{RM} | | | 920 | nC |
| I_{RM} | | | 17 | A |

 Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$

Littelfuse reserves the right to change limits, test conditions and dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|-------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343 | 6,710,405B2 | 6,759,692 | 7,063,975B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

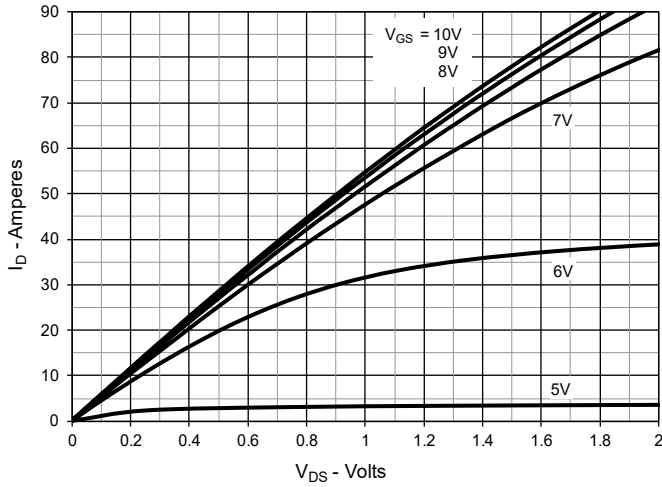


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

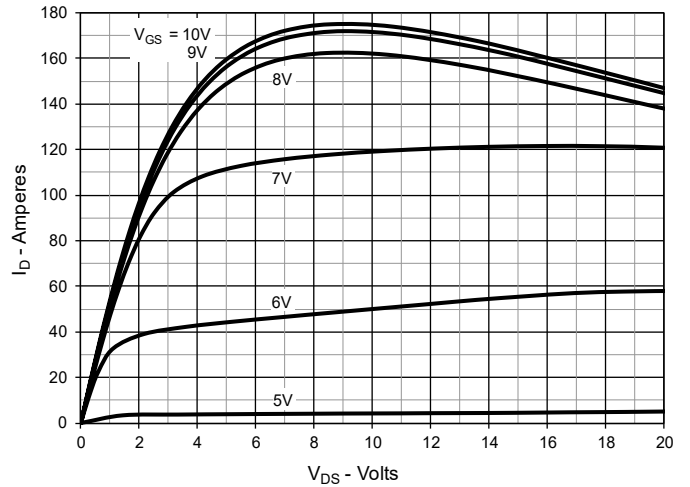


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

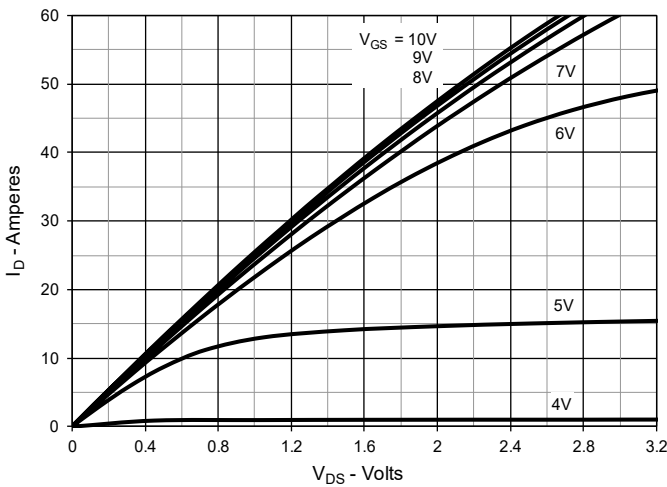


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 30\text{A}$ Value vs. Junction Temperature

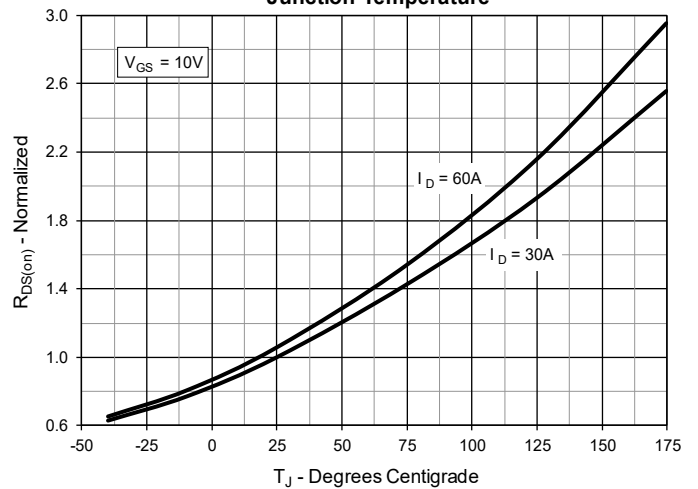


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 30\text{A}$ Value vs. Drain Current

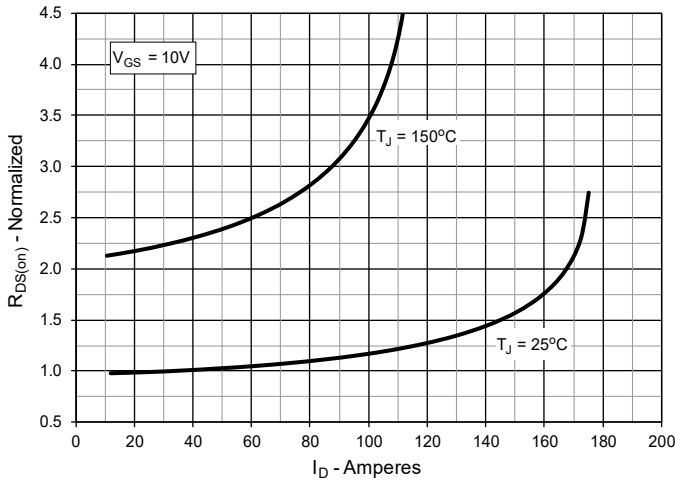


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

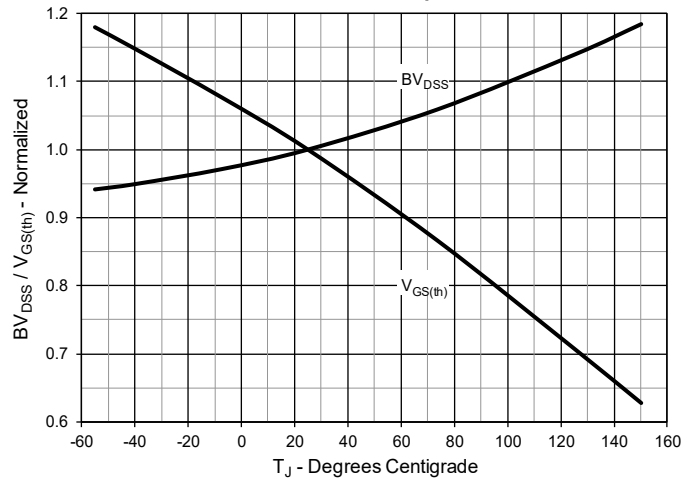


Fig. 7. Maximum Drain Current vs. Case Temperature

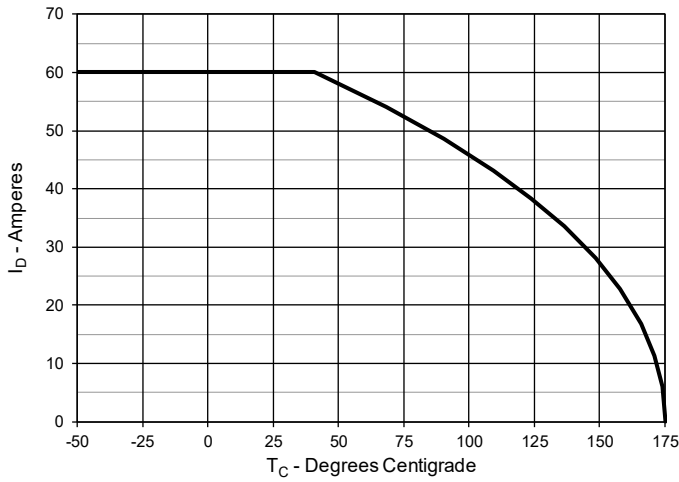


Fig. 8. Input Admittance

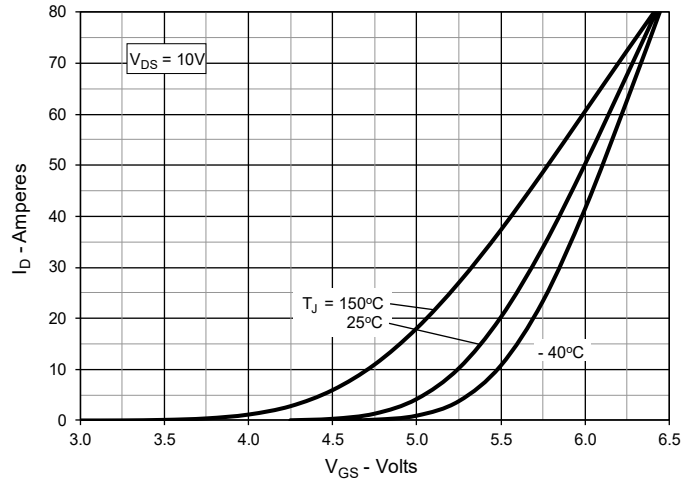


Fig. 9. Transconductance

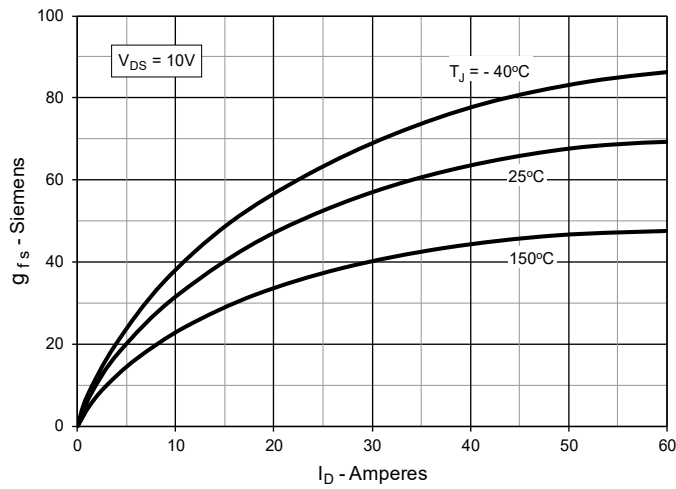


Fig. 10. Forward Voltage Drop of Intrinsic Diode

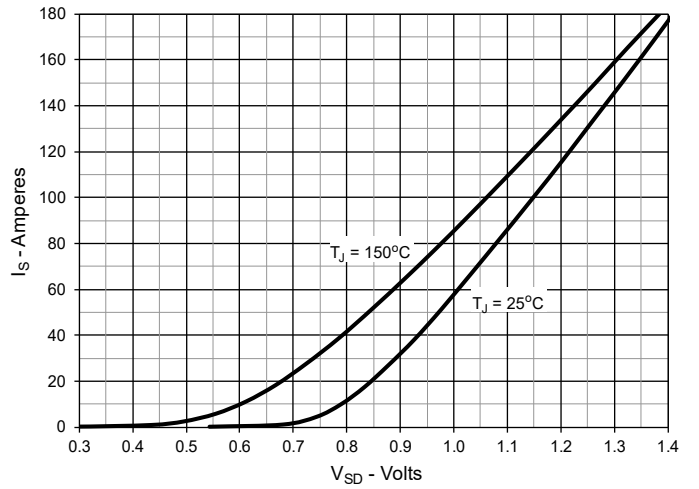


Fig. 11. Gate Charge

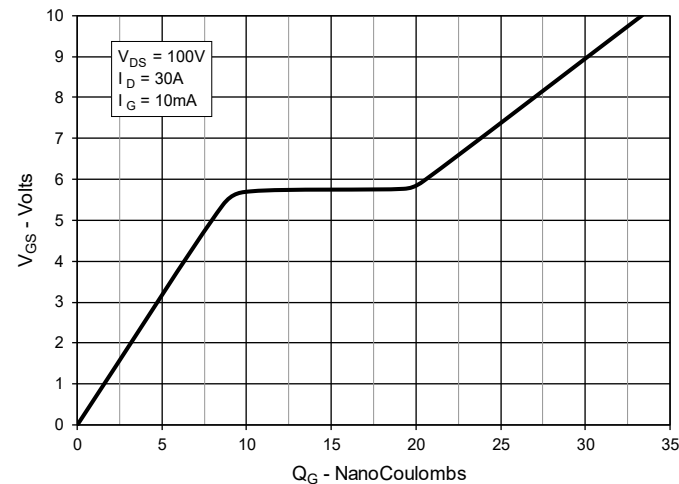


Fig. 12. Capacitance

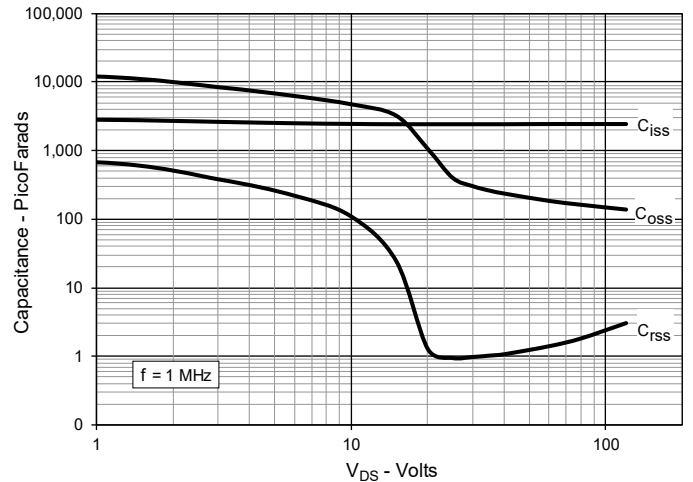


Fig. 13. Output Capacitance Stored Energy

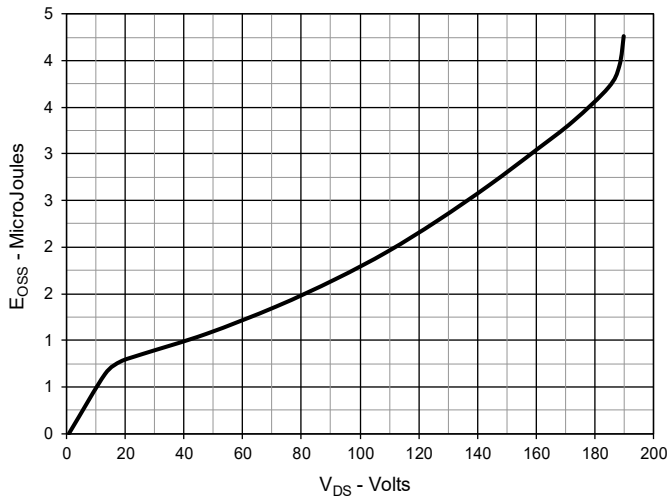


Fig. 14. Forward-Bias Safe Operating Area

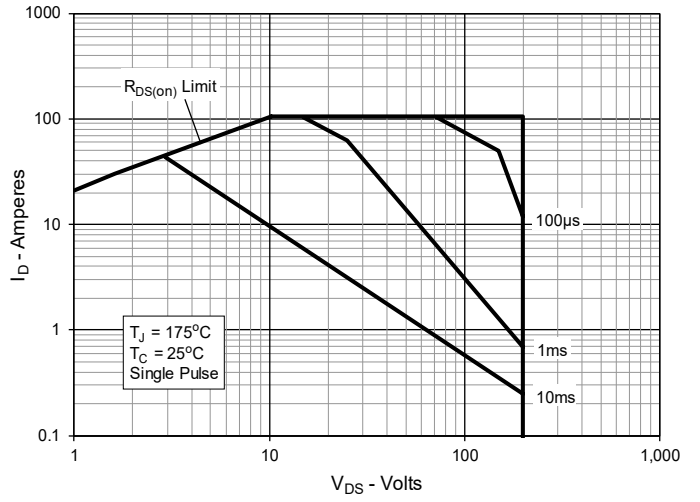


Fig. 15. Maximum Transient Thermal Impedance

